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IN THE UNITED STATES PATENT AND TO DEMARK OFFICE 1 JAN 2005

Applicant:

Josef Böck et al.

Serial No.:

Unknown

(Priority Application No. DE 102 31 407.1)

(International Application No. PCT/EP2003/007553)

Filed:

Herewith

(Priority Date July 11, 2002)

(International Filing Date July 11, 2003)

Docket No.:

I435.121.101/12307US

Title:

BIPOLAR TRANSISTOR

INFORMATION DISCLOSURE STATEMENT

Mail Stop PCT Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56, it is respectfully requested that this Information Disclosure Statement be entered and the documents listed on attached form 1449 be considered by the Examiner and made of record. Any required copies of patents, publications or other documents are enclosed for the Examiner's review. Pursuant to the provisions of M.P.E.P. 609, Applicants further request a copy of the 1449 form, marked as being considered and initialed by the Examiner, be returned with the next Official Communication.

Since this Information Disclosure Statement is being submitted within three months of filing national application; or date of entry of national application; or before the mailing date of the first Office Action on the merits, a fee has not been enclosed. However, if such fee is required, the Patent Office is hereby authorized to charge Deposit Account No. 500471 for fees as set forth under 37 C.F.R. 1.17(p).

T15 Rec'd PCT/PTO 1 1 JAN 2005

Information Disclosine Statement

Applicant: Josef B

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Applicants respectfully request consideration of these references during prosecution of the above-identified matter. The Examiner is invited to contact the Applicants' representative at the below-listed telephone number if there are any questions regarding this Communication or the tendered references.

Respectfully submitted,

Josef Böck et al.,

By their attorneys,

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Dated: January 1.

SED: jan

Reg. No. 38,431

CERTIFICATE UNDER 37 C.F.R. 1.10:

"Express Mail" mailing label number: EV365586985US

Date of Deposit: January 11, 2005

The undersigned hereby certifies that this paper or papers, as described herein, are being deposited in the United States Postal Service "Express Mail Post Office to Addressee" service under 37 C.F.R. 1.10 on the date indicated above and is addressed to: Mail Stop PCT, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 223/3-1450.

Name: Vanessa Carels



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FORM PTO-1449						Docket No.: 1435.121.101/12307US			Serial D./ Unknown 106 Priority Appln. No. DE 102 31 407.1 Int'l Appln. No. PCT/EP2003/007553	
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S						Applicant: Josef Böck et al.				
INFORMATION DISCLOSURE STATEMENT						Filing Date: Herewith Priority Date July 11, 2002 Int'l Filing Date July 11, 2003			Group Art: Unknown	
				U.S. P	ATENT DO	CUMENTS				
Examiner Initial	Document No.	Dat	e		Name		Class		Sub Class	Filing Date If Appropriate
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					76.					

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

DATE CONSIDERED:

EXAMINER: